

B1
or the like is formed on an entire surface of the high dope n-type amorphous silicon layer 57, and a comb-shaped collector 59 of silver (Ag) or the like is formed thereon. The rear surface also has a BSF structure which the intrinsic amorphous silicon layer is sandwiched between the crystalline silicon substrate and the high dope amorphous silicon layer in order to reduce defective on the interface and improve characteristics of the hetero junction interface.

IN THE CLAIMS:

Please amend the claims as follows. A copy of the marked-up original claims is attached to this Response showing the changes, as required by amended 37 C.F.R. §1.121.

1. (Amended) A solar cell module comprising:
a front surface side light transmitting member containing at least sodium;
a rear surface member;
a solar cell element sealed with a sealing resin between the front surface side light transmitting member and the rear surface member, wherein the solar cell element has a semiconductor junction formed with a p-type or n-type crystalline silicon substrate and n-type or p-type semiconductor layer, wherein

B2
the crystalline substrate is positioned on a side of the front surface side light transmitting member, and

the semiconductor layer is positioned on a side of the rear surface side member.

2. (Amended) The solar cell module according to claim 1, wherein the solar cell element is structured so that light enters from a side of the crystalline substrate.
